Supporting Information

Temperature dependent separation of metallic and semiconducting carbon nanotubes using gel agarose chromatography

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1. Raman spectra for DIPS-CNTs



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g. S1.1: Raman spectra of DIPS-CNTs separated at different temperatures; excitation wavelength 514 nm. (a) RBM and (b) D-G regions for top band; (c) RBM and (d) D-G regions for bottom band.



Fig. S1.2: Raman spectra of DIPS-CNTs separated at different temperatures; excitation wavelength 633 nm. (a) RBM and (b) D-G regions for top band; (c) RBM and (d) D-G regions for bottom band.



Fig. S1.3: Raman spectra of DIPS-CNTs separated at different temperatures; excitation wavelength 782 nm. (a) RBM and (b) D-G regions for top band; (c) RBM and (d) D-G regions for bottom band.

2. Raman spectra for AD-CNTs



Figure S2.1: Raman spectra of AD-CNTs separated at different temperatures; excitation wavelength 514 nm. (a) RBM and (b) D-G regions for top band; (c) RBM and (d) D-G regions for bottom band.



Fig. S2.2: Raman spectra of AD-CNTs separated at different temperatures; excitation wavelength 633 nm. (a) RBM and (b) D-G regions for top band; (c) RBM and (d) D-G regions for bottom band.



Fig. S2.3: Raman spectra of AD-CNTs separated at different temperatures; excitation wavelength 782 nm. (a) RBM and (b) D-G regions for top band; (c) RBM and (d) D-G regions for bottom band.

3. Raman spectra of HiPco-SWNTs



Fig. S3.1: Raman spectra of sample HiPco separated at different temperatures; excitation wavelength 514 nm. (a) RBM and (b) D-G regions for top band; (c) RBM and (d) D-G regions for bottom band.



Fig. S3.2: Raman spectra of HiPco-SWNTs separated at different temperatures; excitation wavelength 633 nm. (a) RBM and (b) D-G regions for top band; (c) RBM and (d) D-G regions for bottom band.



Fig. S3.3: Raman spectra of HiPco-SWNTs separated at different temperatures; excitation wavelength 782 nm. (a) RBM and (b) D-G regions for top band; (c) RBM and (d) D-G regions for bottom band.

4. Raman spectra of CoMoCAT-SWNTs



Fig. S4.1: Raman spectra of CoMoCAT-SWNTs separated at different temperatures; excitation wavelength 514 nm. (a) RBM and (b) D-G regions for top band; (c) RBM and (d) D-G regions for bottom band.



Fig. S4.2: Raman spectra of CoMoCAT-SWNTs separated at different temperatures; excitation wavelength 633 nm. (a) RBM and (b) D-G regions for top band; (c) RBM and (d) D-G regions for bottom band.



Fig. S4.3: Raman spectra of CoMoCAT-SWNTs separated at different temperatures; excitation wavelength 782 nm. (a) RBM and (b) D-G regions for top band; (c) RBM and (d) D-G regions for bottom band.





Fig. S5: Ratio of optical absorption of the bottom band to the top band as a function of process temperature. The optical absorption is directly proportional to the SWNT concentration in the respective bands.

Fig. S5 reports the variation of the optical absorption with respect to temperature for each sample at wavelengths corresponding to the optical transition boundaries, i.e. between the excitonic transitions. The absorbance at these wavelengths is the background contribution due to the carbon π -plasmon, which is directly proportional to the SWNT concentration.